

## CLAIMS:

1. A method of fabricating a device using a lithographic process, the method comprising:
  - exposing a part of the resist layer on a substrate; and
  - applying an electric field across the resist, the direction of the field being substantially perpendicular to a plane of the resist layer during the exposing.
2. A method according to claim 1, further comprising applying a layer of conductive material to an upper surface of the resist layer.
3. A method according to claim 2, wherein said electric field is applied by connecting said conductive layer to a fixed potential.
4. A method according to claim 2, wherein said conductive material is metallic.
5. A method according to claim 4, further comprising applying said layer of conductive material to a thickness of less than 50nm.
6. A method according to claim 2, wherein said layer of conductive material overlaps a side or base of the device.
7. A method according to claim 1, further comprising:
  - providing a layer of conductive material on a lower surface of the resist, between the resist and the surface of the device; and
  - applying said electric field during exposure by connecting the layer of conductive material to a fixed potential.
8. A method according to claim 7, wherein said layer of conductive material overlaps a side or base of the device.
9. A method according to claim 1, further comprising:
  - applying a layer of conductive material to an upper surface of the resist;

providing a layer of conductive material on a lower surface of the resist, between the resist and the surface of the device; and

applying said electric field during exposure by applying a potential difference between the two conducting layers.

10. A method according to claim 1, further comprising applying an electric field across the resist by directly coupling the resist to a fixed potential.

11. A method according to claim 8, further comprising incorporating a conducting material into the resist.

12. A method according to claim 1, wherein said radiation is in the extreme ultra-violet range.

13. A method according to claim 1, further comprising orienting the electric field such that the upper surface of the resist layer is at a positive potential with respect to the lower surface.

14. A lithographic apparatus comprising:  
an illumination system for providing a projection beam of radiation;  
a support structure for supporting a patterning device for imparting a pattern to the projection beam;  
a substrate table for holding a substrate;  
a projection system for projecting the patterned beam onto a target portion of the substrate; and  
an electric field generator configured and arranged to apply an electric field across a resist layer provided on a surface of said substrate, the direction of said field being substantially perpendicular to the plane of the resist layer.

15. A method of fabricating a device using a lithographic process, comprising:  
applying a radiation sensitive resist on top of the device, the resist material incorporating a conductive material; and  
exposing a part of the resist to radiation while applying an electric field across the resist.

16. A method of processing a device using a lithographic process, said device comprising a radiation sensitive and conductive resist material, said method comprising:  
exposing the resist material to UV or EUV radiation while applying an electric field across the resist material.